



Features

- 168 Pin JEDEC Standard, Unbuffered 8 Byte Dual In-line Memory Module
- 8Mx64, 8Mx72 Extended Data Out Mode DIMMs
- Performance:

		-50	-60
t_{RAC}	\overline{RAS} Access Time	50ns	60ns
t_{CAC}	\overline{CAS} Access Time	13ns	15ns
t_{AA}	Access Time From Address	25ns	30ns
t_{RC}	Cycle Time	84ns	104ns
t_{HPC}	EDO Mode Cycle Time	20ns	25ns

- Inputs and outputs are LVTTTL (3.3V) compatible
- Single 3.3V \pm 0.3V Power Supply
- Gold contacts

- Optimized for byte-write non-parity, or ECC applications
- System Performance Benefits:
 - Non buffered for increased performance
 - Reduced noise (35 V_{SS}/V_{CC} pins)
 - Byte write, byte read accesses
 - Serial PDs
- Extended Data Out (EDO) Mode, Read-Modify-Write Cycles
- Refresh Modes: \overline{RAS} -Only, CBR and Hidden Refresh
- 4096 refresh cycles distributed across 64ms
- 12/11 addressing (Row/Column)
- Card size: 5.25" x 1.0" x 0.157"
- DRAMS in TSOP Package

Description

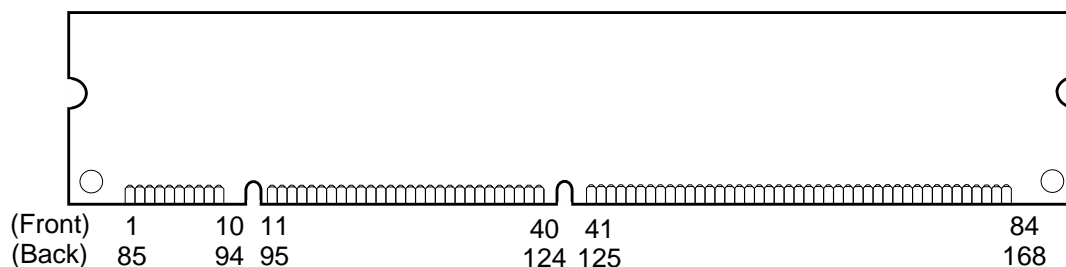
IBM11N8645H/IBM11N8735H are industry standard 168-pin 8-byte Dual In-line Memory Modules (DIMMs) which are organized as 8Mx64 and 8Mx72 high speed memory arrays designed with EDO DRAMs for non-parity or ECC applications. The DIMMs use 8 (x64) or 9 (x72) 8Mx8 EDO DRAMs in TSOP packages. The use of EDO DRAMs allows for a reduction in Page Mode Cycle time from 40ns (Fast Page) to 20ns for 50ns DRAM modules.

The DIMMs use serial presence detects implemented via a serial EEPROM using the two-pin IIC protocol. This communication protocol uses Clock (SCL) and Data I/O (SDA) lines to synchronously

clock data between the master (system logic) and the slave EEPROM device (DIMM). The EEPROM device address pins (SA0-2) are brought out to the DIMM tabs to allow 8 unique DIMM/EEPROM addresses. The first 128 bytes are utilized by the DIMM manufacturer and the second 128 bytes of serial PD data are available to the customer.

All IBM 168-pin DIMMs provide a high performance, flexible 8-byte interface in a 5.25" long space-saving footprint. Related products include the buffered DIMMs (x64 non-parity and x72 ECC Optimized) for applications which can benefit from the on-card buffers.

Card Outline





IBM11N8645H
 IBM11N8735H
 8M x 64/72 DRAM Module

Pin Description

RAS0, RAS2	Row Address Strobe	V _{CC}	Power (3.3V)
CAS0 - CAS7	Column Address Strobe	V _{SS}	Ground
WE0, WE2	Read/write Input	NC	No Connect
OE0, OE2	Output Enable	DU	Don't Use
A0 - A11	Address Inputs	SCL	Serial Presence Detect Clock Input
DQx	Data Input/Output	SDA	Serial Presence Detect Data Input
CBx	Check Bit Data Input/Output	SA0-2	Serial Presence Detect Address Inputs

Pinout

Pin#	Front Side	Pin#	Back Side	Pin#	Front Side	Pin#	Back Side	Pin#	Front Side	Pin#	Back Side	Pin#	Front Side	Pin#	Back Side
1	V _{SS}	85	V _{SS}	22	CB1	106	CB5	43	V _{SS}	127	V _{SS}	64	V _{SS}	148	V _{SS}
2	DQ0	86	DQ32	23	V _{SS}	107	V _{SS}	44	OE2	128	DU	65	DQ21	149	DQ53
3	DQ1	87	DQ33	24	NC	108	NC	45	RAS2	129	NC	66	DQ22	150	DQ54
4	DQ2	88	DQ34	25	NC	109	NC	46	CAS2	130	CAS6	67	DQ23	151	DQ55
5	DQ3	89	DQ35	26	V _{CC}	110	V _{CC}	47	CAS3	131	CAS7	68	V _{SS}	152	V _{SS}
6	V _{CC}	90	V _{CC}	27	WE0	111	DU	48	WE2	132	DU	69	DQ24	153	DQ56
7	DQ4	91	DQ36	28	CAS0	112	CAS4	49	V _{CC}	133	V _{CC}	70	DQ25	154	DQ57
8	DQ5	92	DQ37	29	CAS1	113	CAS5	50	NC	134	NC	71	DQ26	155	DQ58
9	DQ6	93	DQ38	30	RAS0	114	NC	51	NC	135	NC	72	DQ27	156	DQ59
10	DQ7	94	DQ39	31	OE0	115	DU	52	CB2	136	CB6	73	V _{CC}	157	V _{CC}
11	DQ8	95	DQ40	32	V _{SS}	116	V _{SS}	53	CB3	137	CB7	74	DQ28	158	DQ60
12	V _{SS}	96	V _{SS}	33	A0	117	A1	54	V _{SS}	138	V _{SS}	75	DQ29	159	DQ61
13	DQ9	97	DQ41	34	A2	118	A3	55	DQ16	139	DQ48	76	DQ30	160	DQ62
14	DQ10	98	DQ42	35	A4	119	A5	56	DQ17	140	DQ49	77	DQ31	161	DQ63
15	DQ11	99	DQ43	36	A6	120	A7	57	DQ18	141	DQ50	78	V _{SS}	162	V _{SS}
16	DQ12	100	DQ44	37	A8	121	A9	58	DQ19	142	DQ51	79	NC	163	NC
17	DQ13	101	DQ45	38	A10	122	A11	59	V _{CC}	143	V _{CC}	80	NC	164	NC
18	V _{CC}	102	V _{CC}	39	NC	123	NC	60	DQ20	144	DQ52	81	NC	165	SA0
19	DQ14	103	DQ46	40	V _{CC}	124	V _{CC}	61	NC	145	NC	82	SDA	166	SA1
20	DQ15	104	DQ47	41	V _{CC}	125	DU	62	DU	146	DU	83	SCL	167	SA2
21	CB0	105	CB4	42	DU	126	DU	63	NC	147	NC	84	V _{CC}	168	V _{CC}

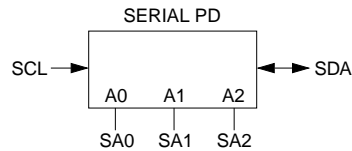
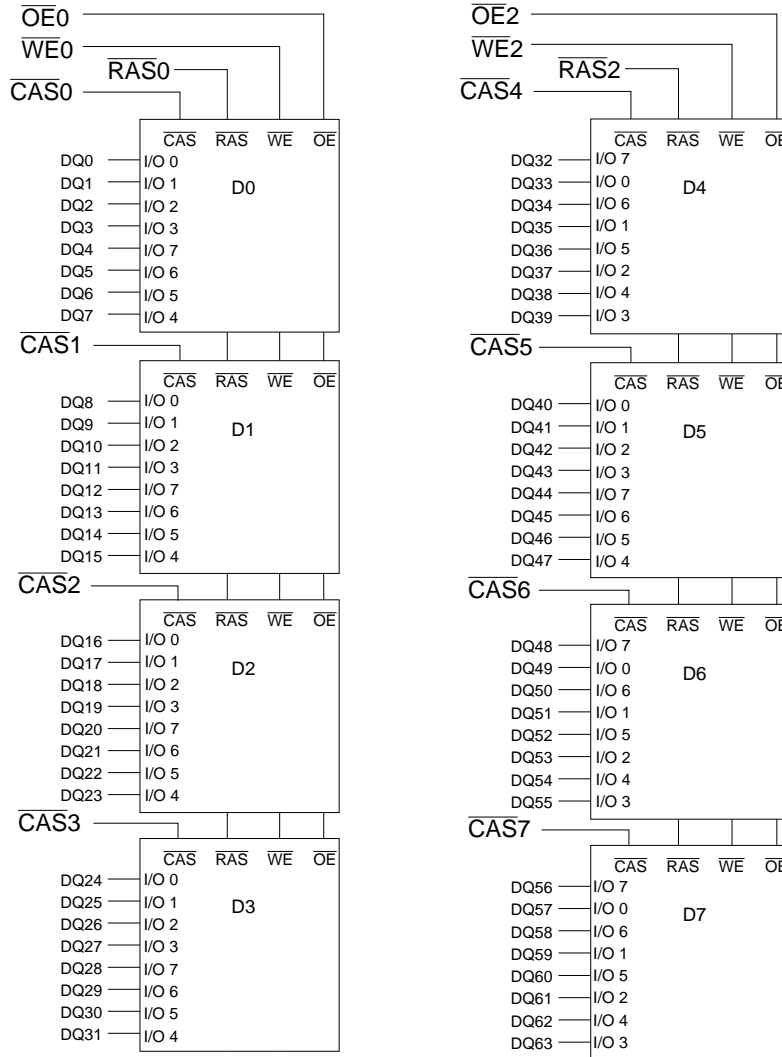
Note: All pin assignments are consistent for all 8 Byte unbuffered versions.

Ordering Information

Part Number	Organization	Speed	Addr.	Leads	Dimension	Power
IBM11N8645HB-50T	8Mx64	50ns	12/11	Gold	5.25"x1.0"x 0.157"	3.3V
IBM11N8645HB-60T		60ns				
IBM11N8735HB-50T	8Mx72	50ns				
IBM11N8735HB-60T		60ns				



x64 DIMM Block Diagram (1 Bank, x4 DRAMs)



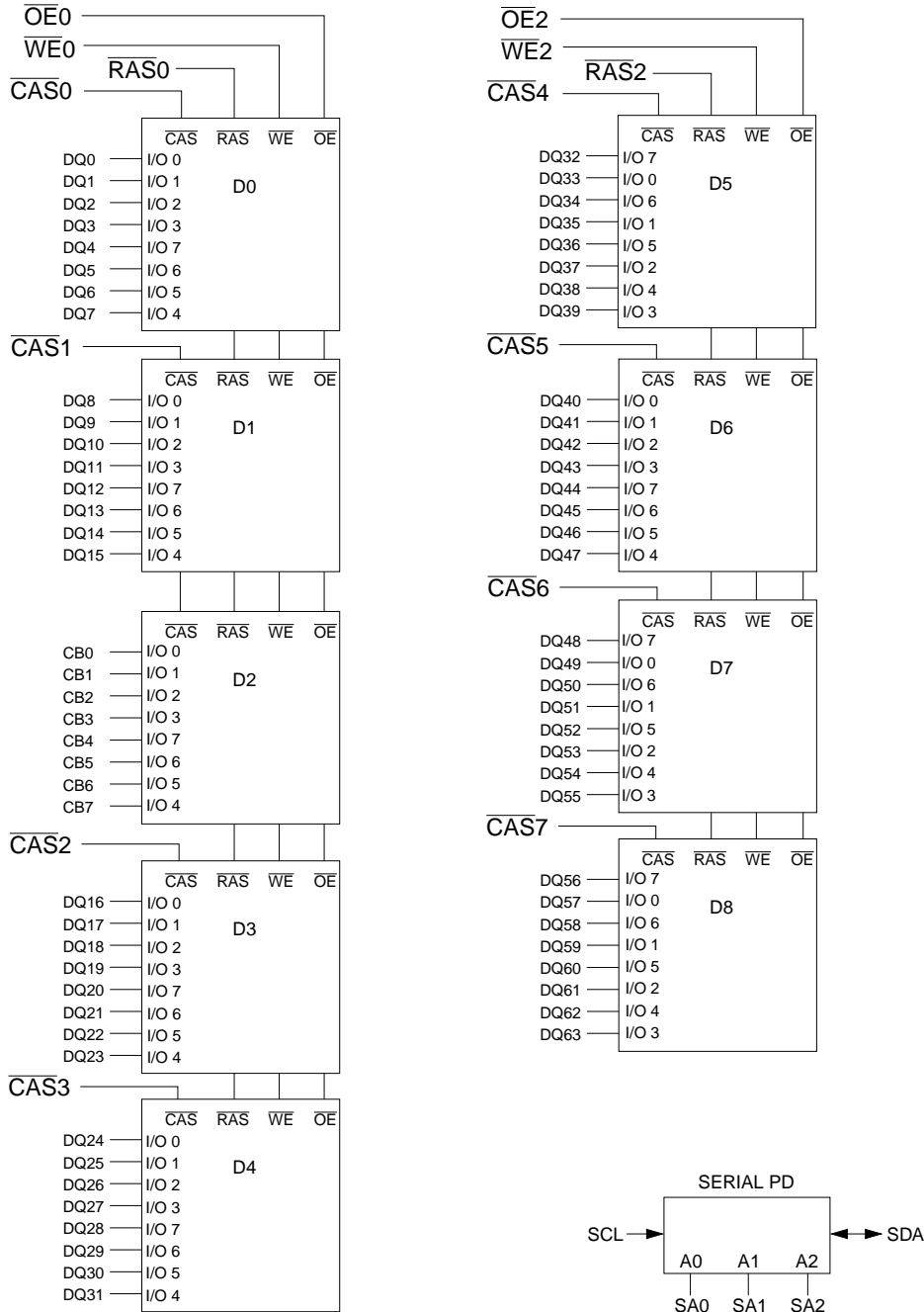
A0 - AN → A0-AN: DRAMS D0 - D7



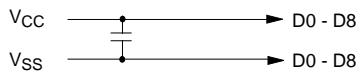


IBM11N8645H
 IBM11N8735H
 8M x 64/72 DRAM Module

x72 ECC DIMM Block Diagram (1 Bank, x8 DRAMs)



A0-AN → A0 - AN: DRAMS D0 - D8





Truth Table

Function	RAS	$\overline{\text{CAS}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	Row Address	Column Address	DQx	
Standby	H	H→X	X	X	X	X	High Impedance	
Read	L	L	H	L	Row	Col	Valid Data Out	
Early-Write	L	L	L	X	Row	Col	Valid Data In	
Late-Write	L	L	H→L	H	Row	Col	Valid Data In	
RMW	L	L	H→L	L→H	Row	Col	Valid Data In/Out	
EDO Page Mode - Read 1st Cycle	L	H→L	H	L	Row	Col	Valid Data Out	
Subsequent Cycles	L	H→L	H	L	N/A	Col	Valid Data Out	
EDO Page Mode - Write 1st Cycle	L	H→L	L	X	Row	Col	Valid Data In	
Subsequent Cycles	L	H→L	L	X	N/A	Col	Valid Data In	
EDO Page Mode - RMW 1st Cycle	L	H→L	H→L	L→H	Row	Col	Valid Data In/Out	
Subsequent Cycles	L	H→L	H→L	L→H	N/A	Col	Valid Data In/Out	
$\overline{\text{RAS}}$ -Only Refresh	L	H	X	X	Row	N/A	High Impedance	
$\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ Refresh	H→L	L	H	X	X	X	High Impedance	
Hidden Refresh	Read	L→H→L	L	H	L	Row	Col	Data Out
	Write	L→H→L	L	H	X	Row	Col	Data In



IBM11N8645H
 IBM11N8735H
 8M x 64/72 DRAM Module

Serial Presence Detect

Byte #	Description	SPD Entry Value	Serial PD Data Entry (Hexadecimal)		
0	Number of Serial PD Bytes Written during Production	128	80		
1	Total Number of Bytes in Serial PD device	256	08		
2	Fundamental Memory Type	EDO	02		
3	Number of Row Addresses on Assembly	12	0C		
4	Number of Column Addresses on Assembly	11	0B		
5	Number of DIMM Banks	1	01		
6 - 7	Data Width of Assembly	8M x 64	x64	4000	
		8M x 72	x72	4800	
8	Voltage Interface Level of this Assembly	LVTTL	01		
9	$\overline{\text{RAS}}$ Access	50ns	50ns	32	
		60ns	60ns	3C	
10	$\overline{\text{CAS}}$ Access	50ns	13ns	0D	
		60ns	15ns	0F	
11	DIMM Configuration Type	8M x 64	Non-Parity	00	
		8M x 72	ECC	02	
12	Refresh Rate/Type	Normal 15.6us	00		
13	Primary DRAM Data Width	x8	08		
14	Error Checking DRAM Data Width	8M x 64	N/A	00	
		8M x 72	x8	08	
15 - 62	Reserved	Undefined	00		
63	Checksum for bytes 0 - 62	Checksum Data	cc		
64 - 71	Manufacturers' JEDEC ID Code	IBM	A400000000000000		
72	Module Manufacturing Location	Toronto, Canada	91		
		Vimercate, Italy	53		
73 - 90	Module Part Number	8M x 64	50ns	ASCII '11N8645HB'R'-50T'	31314E383634354842rr2D35305420202020
			60ns	ASCII '11N8645HB'R'-60T'	31314E383634354842rr2D36305420202020
		8M x 72	50ns	ASCII '11N8735HB'R'-50T'	31314E383733354842rr2D35305420202020
			60ns	ASCII '11N8735HB'R'-60T'	31314E383733354842rr2D36305420202020
91 - 92	Module Revision Code	"R" plus ASCII blank	rr20		
93 - 94	Module Manufacturing Date	Week/Year Code	yyww		
95 - 98	Module Serial Number	Serial Number	ssssssss		
99 - 127	Reserved	Undefined	00		
128 - 255	Open for Customer Use	Undefined	00		

cc = Checksum Data byte, 00-FF (Hex)
 "R" = Alphanumeric revision code, A-Z, 0-9
 rr = ASCII coded revision code byte "R"
 ww = Binary coded decimal week code, 01-52 (Decimal) → 01-34 (Hex)
 yy = Binary coded decimal year code, 00-99 (Decimal) → 00-63 (Hex)
 ss = Serial number data byte, 00-FF (Hex)



Absolute Maximum Ratings

Symbol	Parameter	Rating (3.3V)	Units	Notes	
V_{CC}	Power Supply Voltage	-0.5 to +4.6	V	1	
V_{IN}	Input Voltage	-0.5 to min ($V_{CC} + 0.5$, 4.6)	V	1	
$V_{IN/OUT}$ (SPD)	Input Voltage (Serial PD Device)	-0.3 to +6.5	V	1	
V_{OUT}	Output Voltage	-0.5 to min ($V_{CC} + 0.5$, 4.6)	V	1	
T_{OPR}	Operating Temperature	0 to +70	°C	1	
T_{STG}	Storage Temperature	-55 to +125	°C	1	
P_D	Power Dissipation	x64	3.7	W	1, 2
		x72	5.0		
I_{OUT}	Short Circuit Output Current	50	mA	1	

1. Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated is not implied. Exposure to absolute maximum rating condition for extended periods may affect reliability.
2. P_D Calculated for -60.

Recommended DC Operating Conditions ($T_A = 0$ to 70°C)

Symbol	Parameter	3.3V			Units	Notes
		Min	Typ	Max		
V_{CC}	Supply Voltage	3.0	3.3	3.6	V	1
V_{IH}	Input High Voltage	2.0	—	$V_{CC} + 0.3$	V	1, 2
V_{IL}	Input Low Voltage	-0.3	—	0.8	V	1, 2

1. All voltages referenced to V_{SS} .
2. V_{IH} may overshoot to $V_{CC} + 1.2\text{V}$ for pulse widths of $\leq 4.0\text{ns}$ (or $V_{CC} + 1.0\text{V}$ for $\leq 8.0\text{ns}$). Additionally, V_{IL} may undershoot to -2.0V for pulse widths $\leq 4.0\text{ns}$ (or -1.0V for $\leq 8.0\text{ns}$). Pulse widths measured at 50% points with amplitude measured peak to DC reference.

Capacitance ($T_A = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3\text{V} \pm 0.3\text{V}$)

Symbol	Parameter	Max		Units
		x64	x72	
C_{I1}	Input Capacitance (A0-A11)	60	65	pF
C_{I2}	Input Capacitance ($\overline{\text{RAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$)	50	55	pF
C_{I3}	Input Capacitance ($\overline{\text{CAS}}$)	17	22	pF
C_{I4}	Input Capacitance ($\overline{\text{SCL}}$, SA0-3)	8	8	pF
C_{IO1}	Input/Output Capacitance (DQx, CBx)	13	13	pF
C_{IO2}	Input/Output Capacitance (SDA)	10	10	pF



IBM11N8645H
 IBM11N8735H
 8M x 64/72 DRAM Module

DC Electrical Characteristics ($T_A = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3\text{V} \pm 0.3\text{V}$)

Symbol	Parameter	x64		x72		Units	Notes
		Min.	Max.	Min.	Max.		
I _{CC1}	Operating Current Average Power Supply Operating Current (RAS, CAS, Address Cycling: $t_{RC} = t_{RC \text{ min.}}$)	-50	—	N/A	—	1386	1, 2, 3
		-60	—	1040	—	1170	
I _{CC2}	Standby Current (TTL) Power Supply Standby Current (RAS = CAS = V _{IH})	—	16	—	18	mA	
I _{CC3}	RAS Only Refresh Current Average Power Supply Current, RAS Only Mode (RAS Cycling, CAS = V _{IH} : $t_{RC} = t_{RC \text{ min}}$)	-50	—	N/A	—	1215	1, 3
		-60	—	880	—	990	
I _{CC4}	EDO Page Mode Current Average Power Supply Current, EDO Page Mode (RAS = V _{IL} , CAS, Address Cycling: $t_{HPC} = t_{HPC \text{ min}}$)	-50	—	N/A	—	810	1, 2, 3
		-60	—	640	—	720	
I _{CC5}	Standby Current (CMOS) Power Supply Standby Current (RAS = CAS = V _{CC} - 0.2V)	—	8	—	9	mA	
I _{CC6}	CAS Before RAS Refresh Current Average Power Supply Current, CAS Before RAS Mode (RAS, CAS, Cycling: $t_{RC} = t_{RC \text{ min}}$)	-50	—	N/A	—	1305	1, 3
		-60	—	960	—	1080	
I _{I(L)}	Input Leakage Current Input Leakage Current, any input ($0.0 \leq V_{IN} \leq (V_{CC} + 0.3\text{V})$), All Other Pins Not Under Test = 0V	RAS, WE, OE	-8	+8	-9	+9	μA
		CAS	-2	+2	-4	+4	
		Address	-16	+16	-18	+18	
I _{O(L)}	Output Leakage Current (D _{OUT} is disabled, $0.0 \leq V_{OUT} \leq V_{CC}$)	-2	+2	-2	+2	μA	
V _{OH}	Output Level (TTL) Output "H" Level Voltage (I _{OUT} = -2mA)	2.4	V _{CC}	2.4	V _{CC}	V	
V _{OL}	Output Level (TTL) Output "L" Level Voltage (I _{OUT} = +2mA)	0.0	0.4	0.0	0.4	V	

1. I_{CC1}, I_{CC3}, I_{CC4} and I_{CC6} depend on cycle rate.
2. I_{CC1} and I_{CC4} depend on output loading. Specified values are obtained with the output open.
3. Address can be changed once or less while RAS = V_{IL}. In the case of I_{CC4}, it can be changed once or less when CAS = V_{IH}.


AC Characteristics ($T_A = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3\text{V} \pm 0.3\text{V}$)

- V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} and V_{IL} .
- An initial pause of $200\mu\text{s}$ is required after power-up followed by 8 $\overline{\text{RAS}}$ only refresh cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh cycles instead of 8 $\overline{\text{RAS}}$ only refresh cycles is required..
- AC measurements assume $t_T = 2\text{ns}$.

Read, Write, Read-Modify-Write and Refresh Cycles (Common Parameters)

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{RC}	Random Read or Write Cycle Time	84	—	104	—	ns	
t_{RP}	$\overline{\text{RAS}}$ Precharge Time	30	—	40	—	ns	
t_{CP}	$\overline{\text{CAS}}$ Precharge Time	8	—	10	—	ns	
t_{RAS}	$\overline{\text{RAS}}$ Pulse Width	50	10K	60	10K	ns	
t_{CAS}	$\overline{\text{CAS}}$ Pulse Width	8	10K	10	10K	ns	
t_{ASR}	Row Address Setup Time	0	—	0	—	ns	
t_{RAH}	Row Address Hold Time	10	—	10	—	ns	
t_{ASC}	Column Address Setup Time	0	—	0	—	ns	
t_{CAH}	Column Address Hold Time	8	—	10	—	ns	
t_{RCD}	$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Delay Time	14	37	14	45	ns	1
t_{RAD}	$\overline{\text{RAS}}$ to Column Address Delay Time	12	25	12	30	ns	2
t_{RSH}	$\overline{\text{RAS}}$ Hold Time	8	—	10	—	ns	
t_{CSH}	$\overline{\text{CAS}}$ Hold Time	43	—	50	—	ns	
t_{CRP}	$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ Precharge Time	5	—	5	—	ns	
t_{ODD}	$\overline{\text{OE}}$ to D_{IN} Delay Time	15	—	15	—	ns	3
t_{DZO}	$\overline{\text{OE}}$ Delay Time from D_{IN}	0	—	0	—	ns	4
t_{DZC}	$\overline{\text{CAS}}$ Delay Time from D_{IN}	0	—	0	—	ns	4
t_T	Transition Time (Rise and Fall)	2	30	1	30	ns	

- Operation within the $t_{RCD}(\text{max})$ limit ensures that $t_{RAC}(\text{max})$ can be met. The $t_{RCD}(\text{max})$ is specified as a reference point only: If t_{RCD} is greater than the specified $t_{RCD}(\text{max})$ limit, then access time is controlled by t_{CAC} .
- Operation within the $t_{RAD}(\text{max})$ limit ensures that $t_{RAC}(\text{max})$ can be met. The $t_{RAD}(\text{max})$ is specified as a reference point only: If t_{RAD} is greater than the specified $t_{RAD}(\text{max})$ limit, then access time is controlled by t_{AA} .
- Either t_{CDD} or t_{ODD} must be satisfied.
- Either t_{DZC} or t_{DZO} must be satisfied.



IBM11N8645H
 IBM11N8735H
 8M x 64/72 DRAM Module

Write Cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{WCS}	Write Command Set Up Time	0	—	0	—	ns	1
t_{WCH}	Write Command Hold Time	7	—	10	—	ns	
t_{WP}	Write Command Pulse Width	7	—	10	—	ns	
t_{RWL}	Write Command to \overline{RAS} Lead Time	7	—	10	—	ns	
t_{CWL}	Write Command to \overline{CAS} Lead Time	7	—	10	—	ns	
t_{DS}	D_{IN} Setup Time	0	—	0	—	ns	2
t_{DH}	D_{IN} Hold Time	7	—	10	—	ns	2

- t_{WCS} , t_{RWD} , t_{CWD} , and t_{AWD} are not restrictive parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}(\text{min.})$, the entire cycle is an early write cycle and the data pin will remain open circuit (high impedance) through the entire cycle; If $t_{RWD} \geq t_{RWD}(\text{min.})$, $t_{CWD} \geq t_{CWD}(\text{min.})$ and $t_{AWD} \geq t_{AWD}(\text{min.})$, the cycle is a Read-Modify-Write cycle and the data will contain read from the selected cell: If neither of the above sets of conditions are met, the condition of the data (at access time) is indeterminate.
- Data-in set-up and hold is measured from the latter of the two timings, \overline{CAS} or \overline{WE} .



Read Cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{RAC}	Access Time from \overline{RAS}	—	50	—	60	ns	1, 2
t_{CAC}	Access Time from \overline{CAS}	—	13	—	15	ns	1, 2
t_{AA}	Access Time from Address	—	25	—	30	ns	1, 2
t_{OEA}	Access Time from \overline{OE}	—	13	—	15	ns	1, 2
t_{RCS}	Read Command Setup Time	0	—	0	—	ns	
t_{RCH}	Read Command Hold Time to \overline{CAS}	0	—	0	—	ns	3
t_{RRH}	Read Command Hold Time to \overline{RAS}	0	—	0	—	ns	3
t_{RAL}	Column Address to \overline{RAS} Lead Time	25	—	30	—	ns	
t_{CLZ}	\overline{CAS} to Output in Low-Z	0	—	0	—	ns	
t_{OES}	\overline{OE} setup time prior to \overline{CAS}	5	—	5	—	ns	
t_{ORD}	\overline{OE} setup time prior to \overline{RAS} (Hidden Refresh)	0	—	0	—	ns	
t_{CDD}	\overline{CAS} to D_{IN} Delay Time	13	—	15	—	ns	5
t_{OEZ}	Output Buffer Turn-off Delay from \overline{OE}	—	13	—	15	ns	4
t_{OFF}	Output Buffer Turn-off Delay	—	13	—	15	ns	4, 6

1. Measured with the specified current load and 100pF.
2. Access time is determined by the latter of t_{RAC} , t_{CAC} , t_{CPA} , t_{AA} , t_{OEA} .
3. Either t_{RCH} or t_{RRH} must be satisfied.
4. t_{OFF} (max) and t_{OEZ} (max) define the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
5. Either t_{CDD} or t_{ODD} must be satisfied.
6. t_{OFF} is referenced from the rising edge of \overline{RAS} or \overline{CAS} , whichever is last.



IBM11N8645H
 IBM11N8735H
 8M x 64/72 DRAM Module

Read-Modify-Write Cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{RWC}	Read-Modify-Write Cycle Time	110	—	135	—	ns	
t_{RWD}	\overline{RAS} to \overline{WE} Delay Time	67	—	79	—	ns	1
t_{CWD}	\overline{CAS} to \overline{WE} Delay Time	30	—	34	—	ns	1
t_{AWD}	Column Address to \overline{WE} Delay Time	42	—	49	—	ns	1
t_{OEH}	\overline{OE} Command Hold Time	7	—	10	—	ns	

1. t_{WCS} , t_{RWD} , t_{CWD} , and t_{AWD} are not restrictive parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}(\text{min.})$, the entire cycle is an early write cycle and the data pin will remain open circuit (high impedance) through the entire cycle; If $t_{RWD} \geq t_{RWD}(\text{min.})$, $t_{CWD} \geq t_{CWD}(\text{min.})$ and $t_{AWD} \geq t_{AWD}(\text{min.})$, the cycle is a Read-Modify-Write cycle and the data will contain read from the selected cell: If neither of the above sets of conditions are met, the condition of the data (at access time) is indeterminate.

EDO Mode Cycle

Symbol	Parameter	-50		-60		Units	Notes
		Min.	Max.	Min.	Max.		
t_{HCAS}	\overline{CAS} Pulse Width (EDO Page Mode)	8	10K	10	10K	ns	
t_{HPC}	EDO Page Mode Cycle Time (Read/Write)	20	—	25	—	ns	
t_{HPRWC}	EDO Page Mode Read Modify Write Cycle Time	51	—	60	—	ns	
t_{DOH}	Data-out Hold Time from \overline{CAS}	5	—	5	—	ns	
t_{WHZ}	Output buffer Turn-Off Delay from \overline{WE}	0	10	0	10	ns	
t_{WPZ}	\overline{WE} Pulse Width to Output Disable at \overline{CAS} High	7	—	10	—	ns	
t_{CPRH}	\overline{RAS} Hold Time from \overline{CAS} Precharge	30	—	35	—	ns	
t_{CPA}	Access Time from \overline{CAS} Precharge	—	28	—	35	ns	1
t_{RASP}	EDO Page Mode \overline{RAS} Pulse Width	50	125K	60	200K	ns	
t_{OEP}	\overline{OE} High Pulse Width	5	—	10	—	ns	
t_{OEHC}	\overline{OE} High Hold Time from \overline{CAS} High	5	—	10	—	ns	

1. Measured with the specified current load and 100pF at $V_{OL} = 0.8V$ and $V_{OH} = 2.0V$.



Refresh Cycle

Symbol	Parameter	-50		-60		Unit	Notes
		Min	Max	Min	Max		
t_{CHR}	\overline{CAS} Hold Time (\overline{CAS} before \overline{RAS} Refresh Cycle)	10	—	10	—	ns	
t_{CSR}	\overline{CAS} Setup Time (\overline{CAS} before \overline{RAS} Refresh Cycle)	5	—	5	—	ns	
t_{WRP}	\overline{WE} Setup Time (\overline{CAS} before \overline{RAS} Refresh Cycle)	10	—	10	—	ns	
t_{WRH}	\overline{WE} Hold Time (\overline{CAS} before \overline{RAS} Refresh Cycle)	10	—	10	—	ns	
t_{RPC}	\overline{RAS} Precharge to \overline{CAS} Hold Time	5	—	5	—	ns	
t_{REF}	Refresh Period	—	64	—	64	ms	1

1. 4096 refreshes are required every 64ms.

Presence Detect Read and Write Cycle

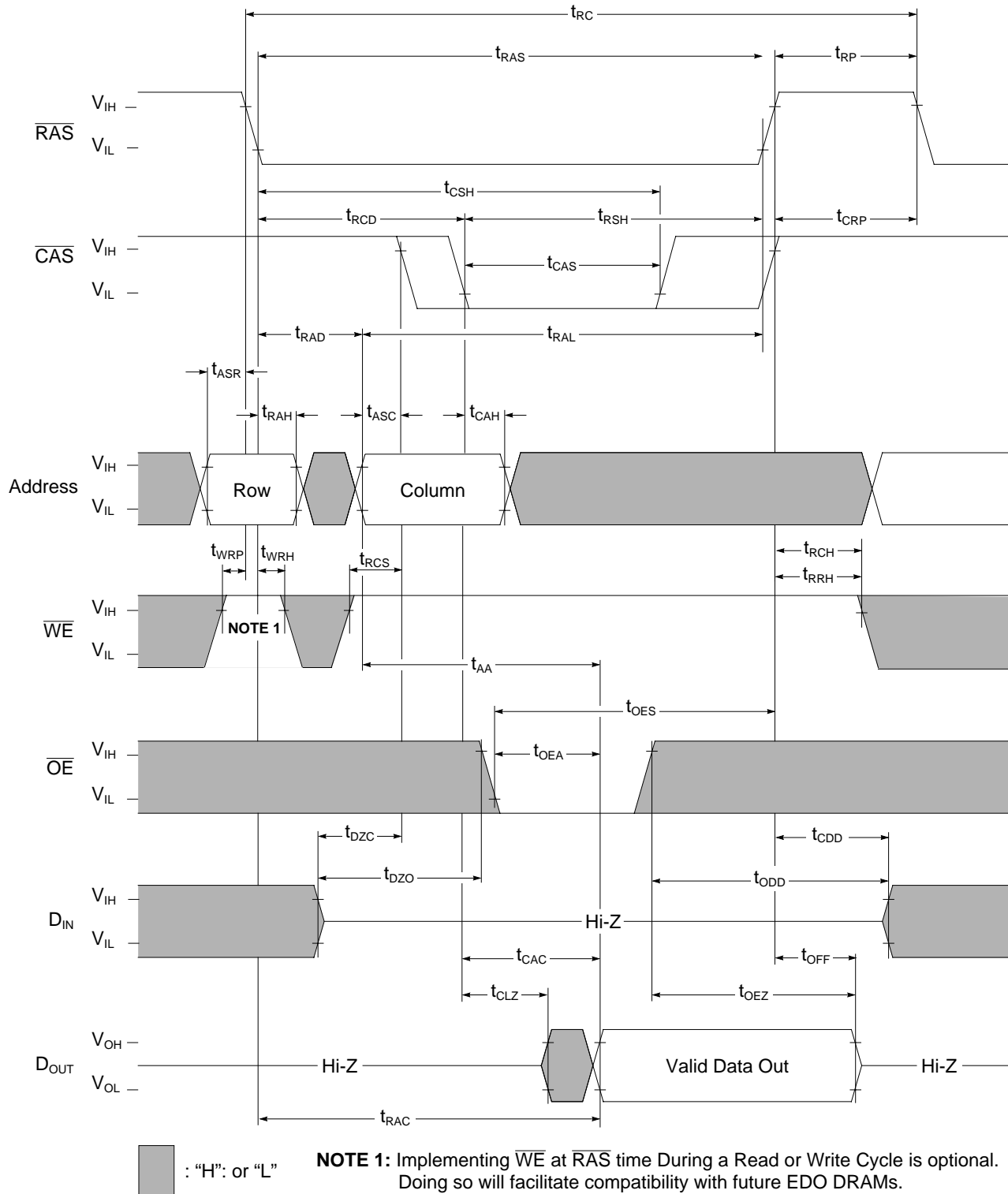
Symbol	Parameter	Min	Max	Unit	Notes
f_{SCL}	SCL Clock Frequency		100	KHZ	
T_I	Noise Suppression Time Constant at SCL, SDA Inputs		100	ns	
t_{AA}	SCL Low to SDA Data Out Valid	0.3	3.5	μ s	
t_{BUF}	Time the Bus Must Be Free before a New Transmission Can Start	4.7		μ s	
$t_{HD:STA}$	Start Condition Hold Time	4.0		μ s	
t_{LOW}	Clock Low Period	4.7		μ s	
t_{HIGH}	Clock High Period	4.0		μ s	
$t_{SU:STA}$	Start Condition Setup Time(for a Repeated Start Condition)	4.7		μ s	
$t_{HD:DAT}$	Data in Hold Time	0		μ s	
$t_{SU:DAT}$	Data in Setup Time	250		ns	
t_r	SDA and SCL Rise Time		1	μ s	
t_f	SDA and SCL Fall Time		300	ns	
$t_{SU:STO}$	Stop Condition Setup Time	4.7		μ s	
t_{DH}	Data Out Hold Time	300		ns	
t_{WR}	Write Cycle Time		15	ms	1

1. The write cycle time(t_{WR}) is the time from a valid stop condition of a write sequence to the end of the internal erase/program cycle. During the write cycle, the bus interface circuits are disabled, SDA is allowed to remain high per the bus-level pull-up resistor, and the device does not respond to its slave address.



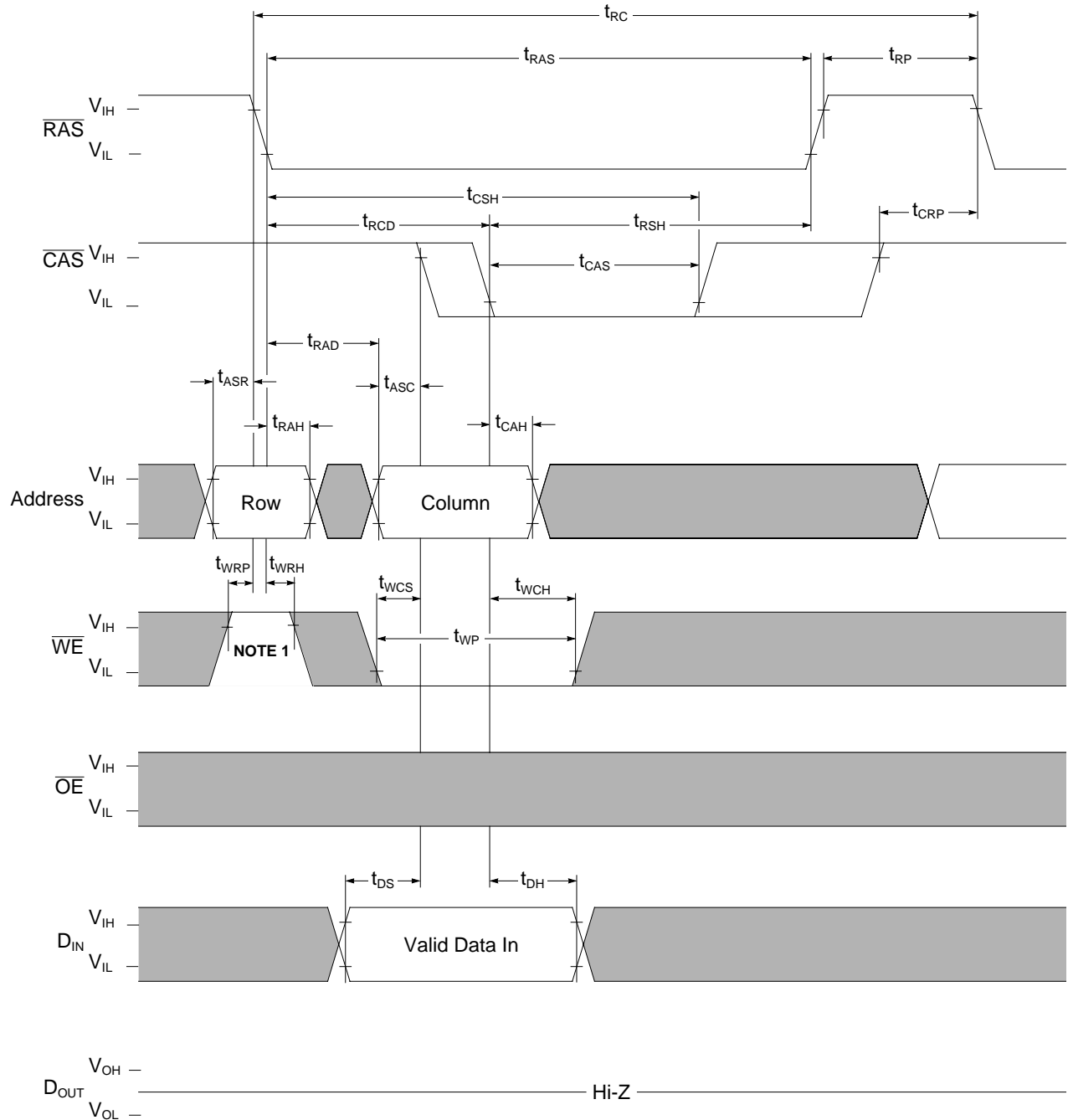
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Read Cycle





Write Cycle (Early Write)

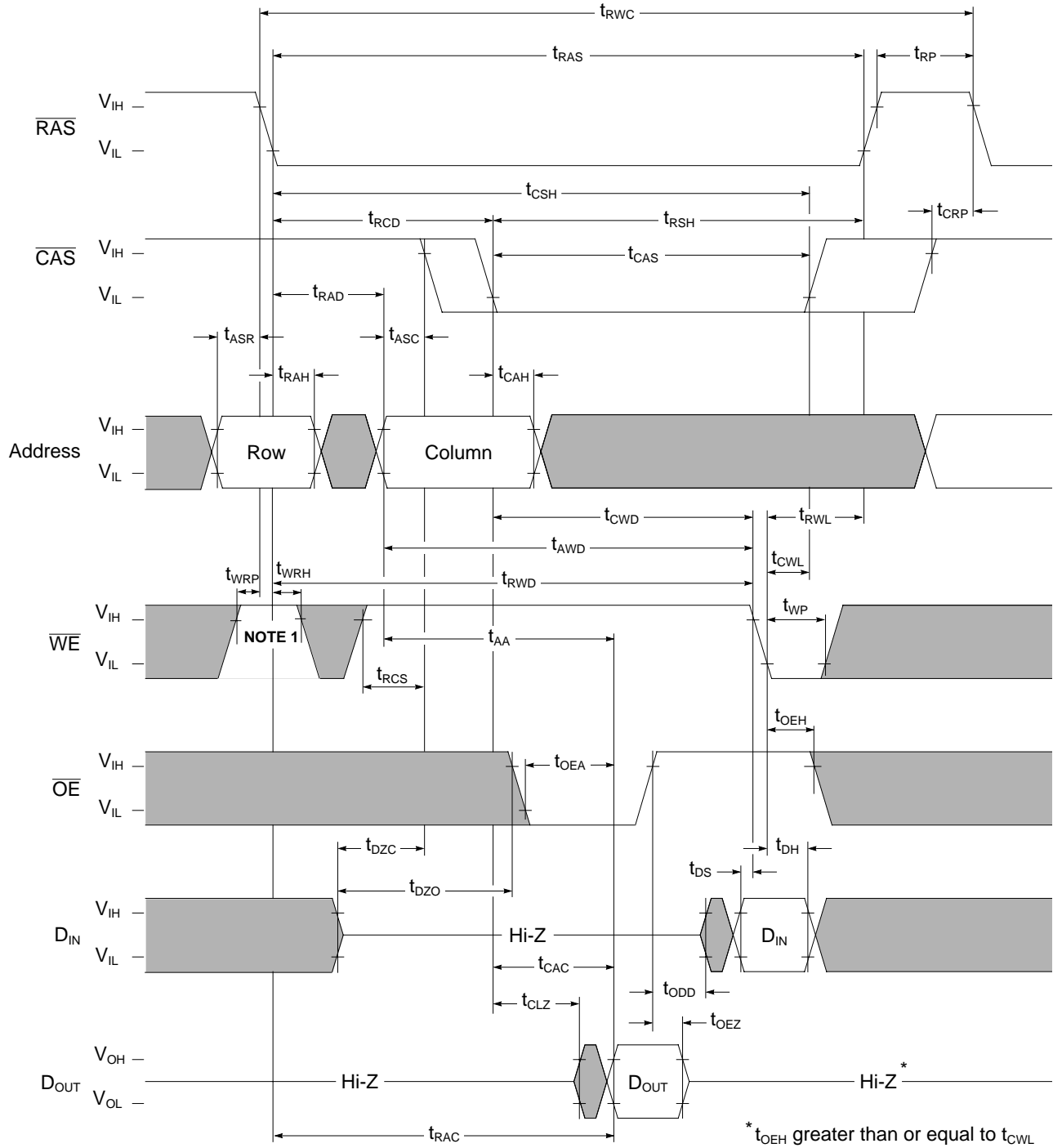


■ : "H" or "L"

NOTE 1: Implementing \overline{WE} at \overline{RAS} time During a Read or Write Cycle is optional. Doing so will facilitate compatibility with future EDO DRAMs.



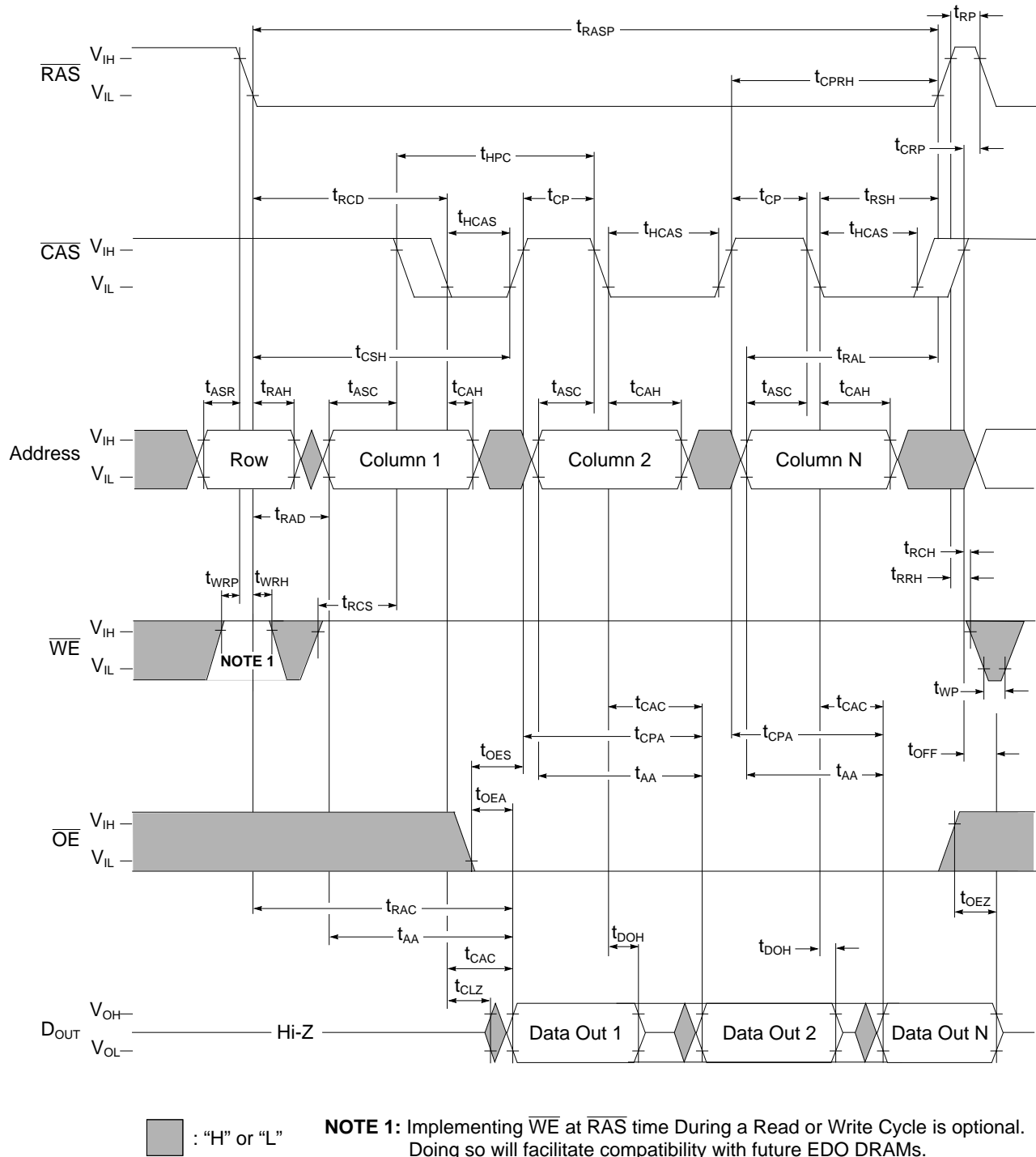
Read-Modify-Write-Cycle



■ : "H" or "L"

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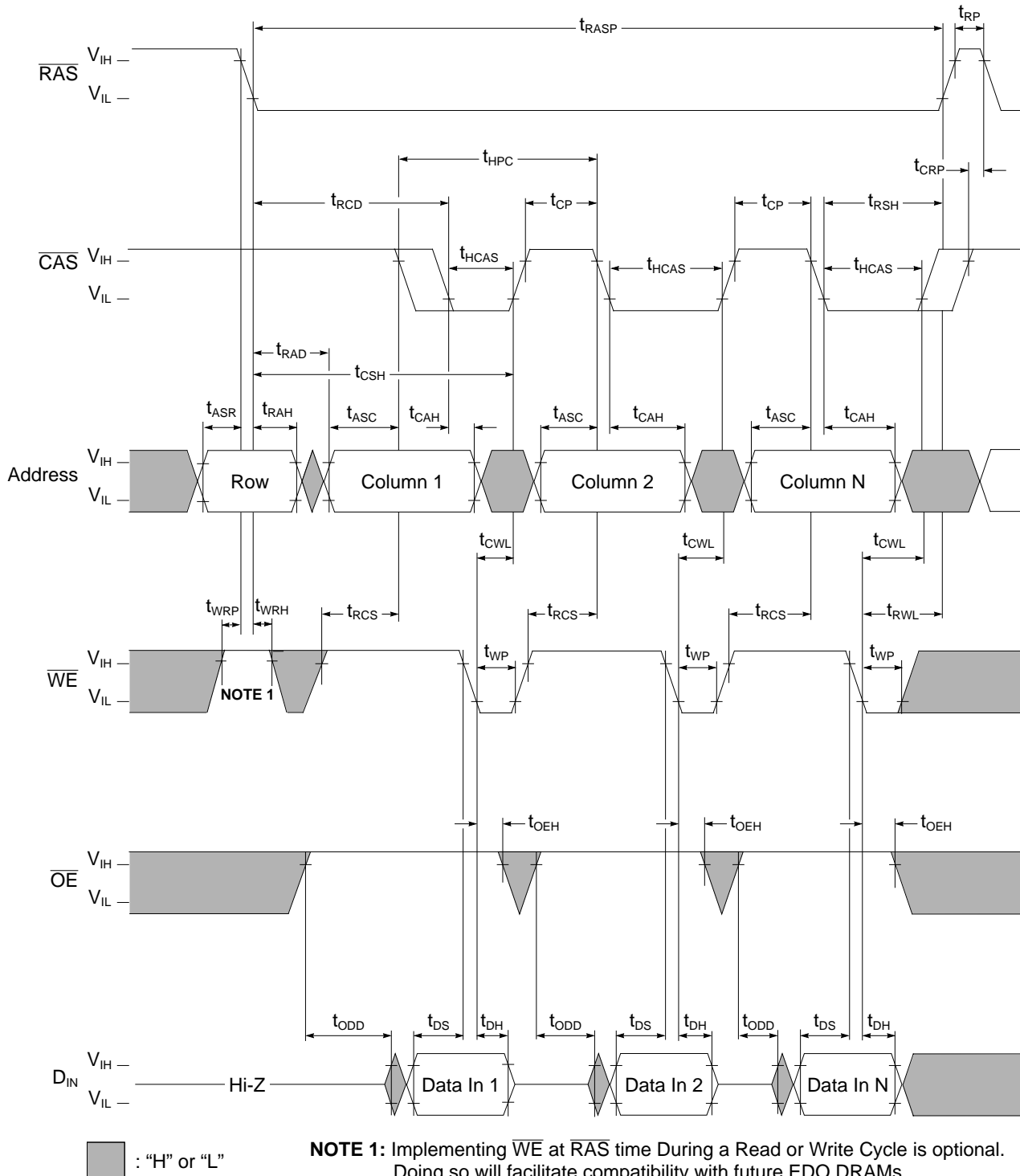
EDO Page Mode Read Cycle





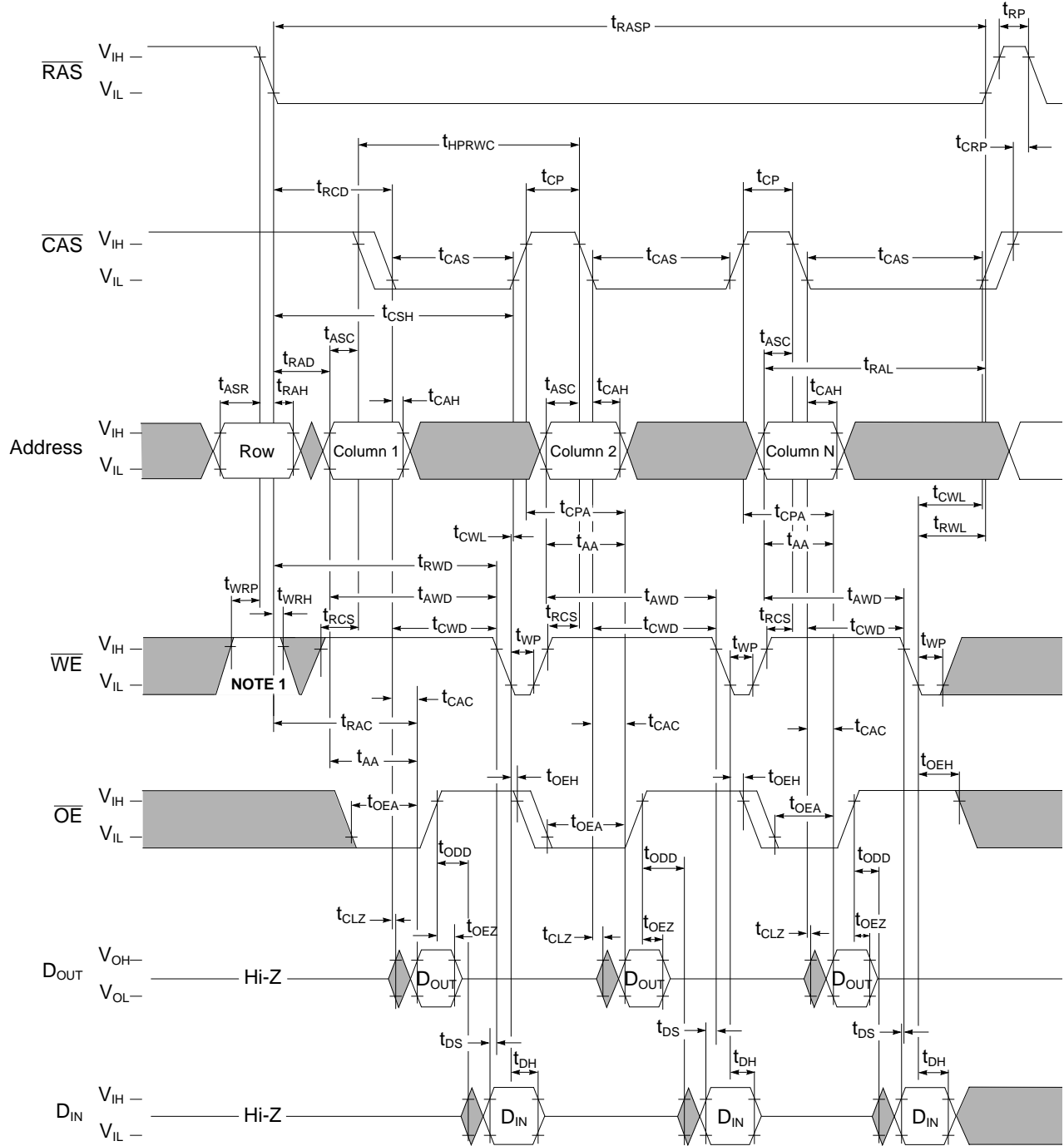
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EDO Page Mode Late Write Cycle





EDO Page Mode Read Modify Write Cycle



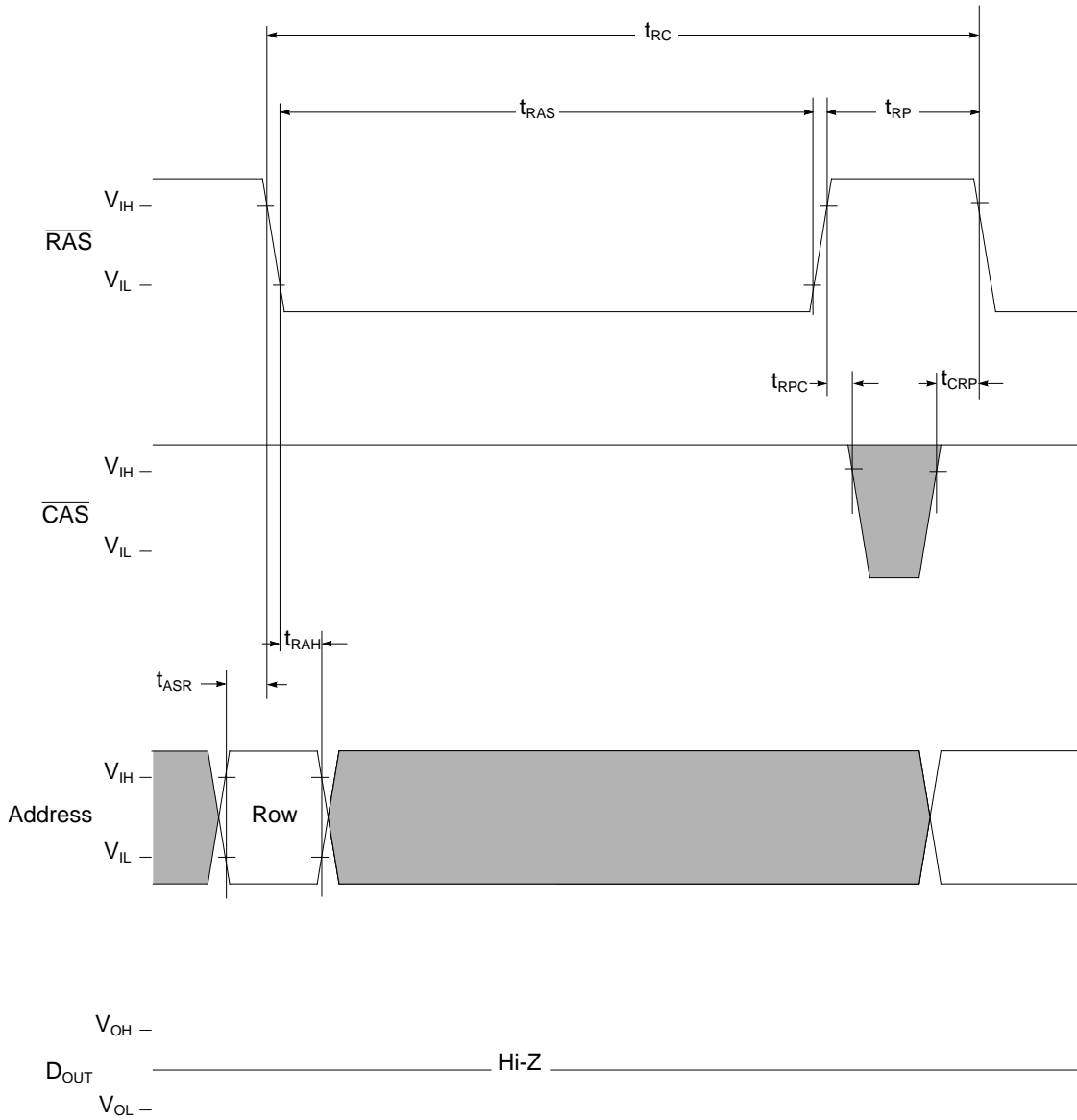
■ : "H" or "L"


NOTE 1: Implementing \overline{WE} at \overline{RAS} time During a Read or Write Cycle is optional. Doing so will facilitate compatibility with future EDO DRAMs.



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RAS Only Refresh Cycle

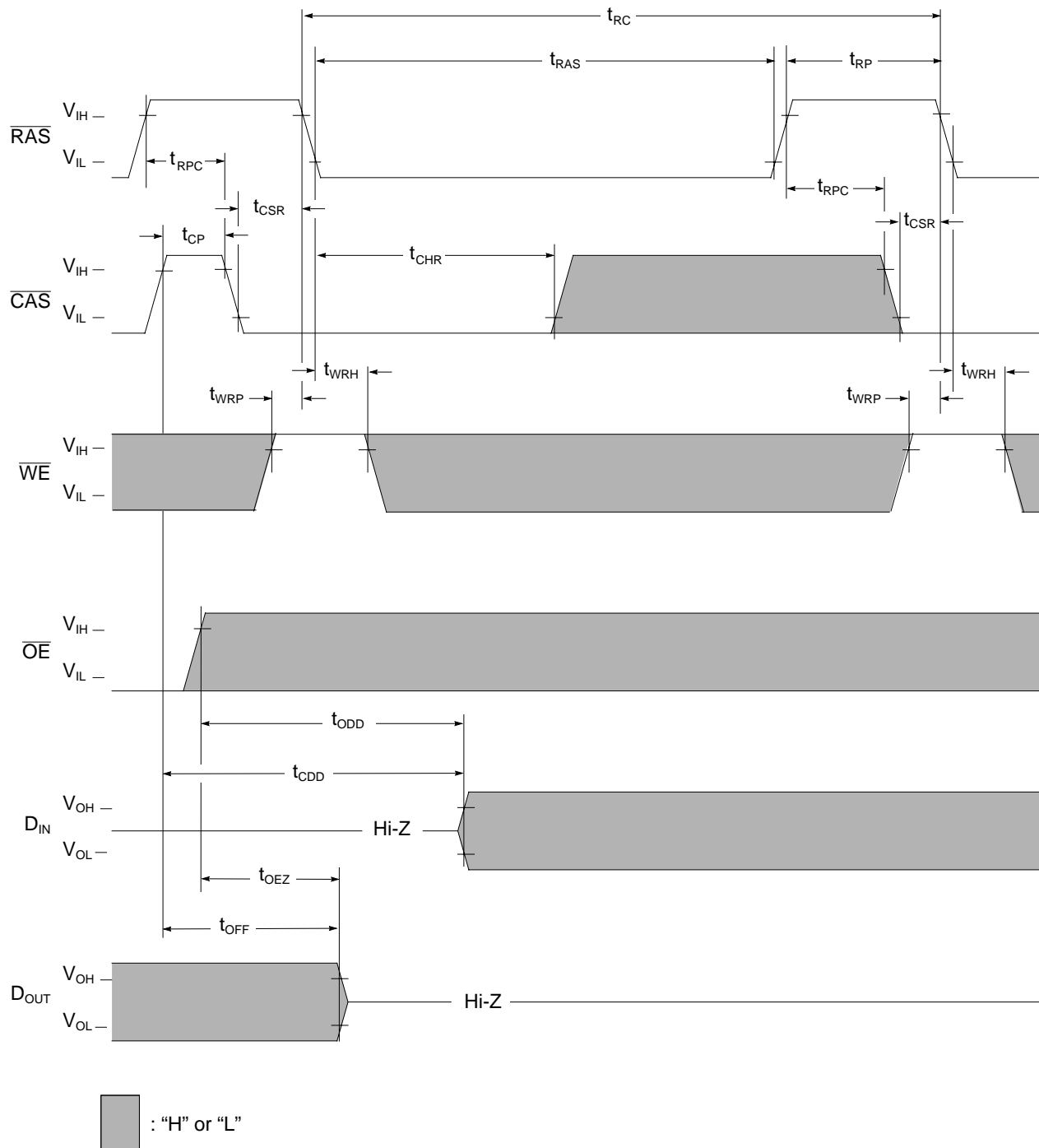


 : "H" or "L"

Note: \overline{WE} , \overline{OE} , D_{IN} are "H" or "L"



CAS Before RAS Refresh Cycle

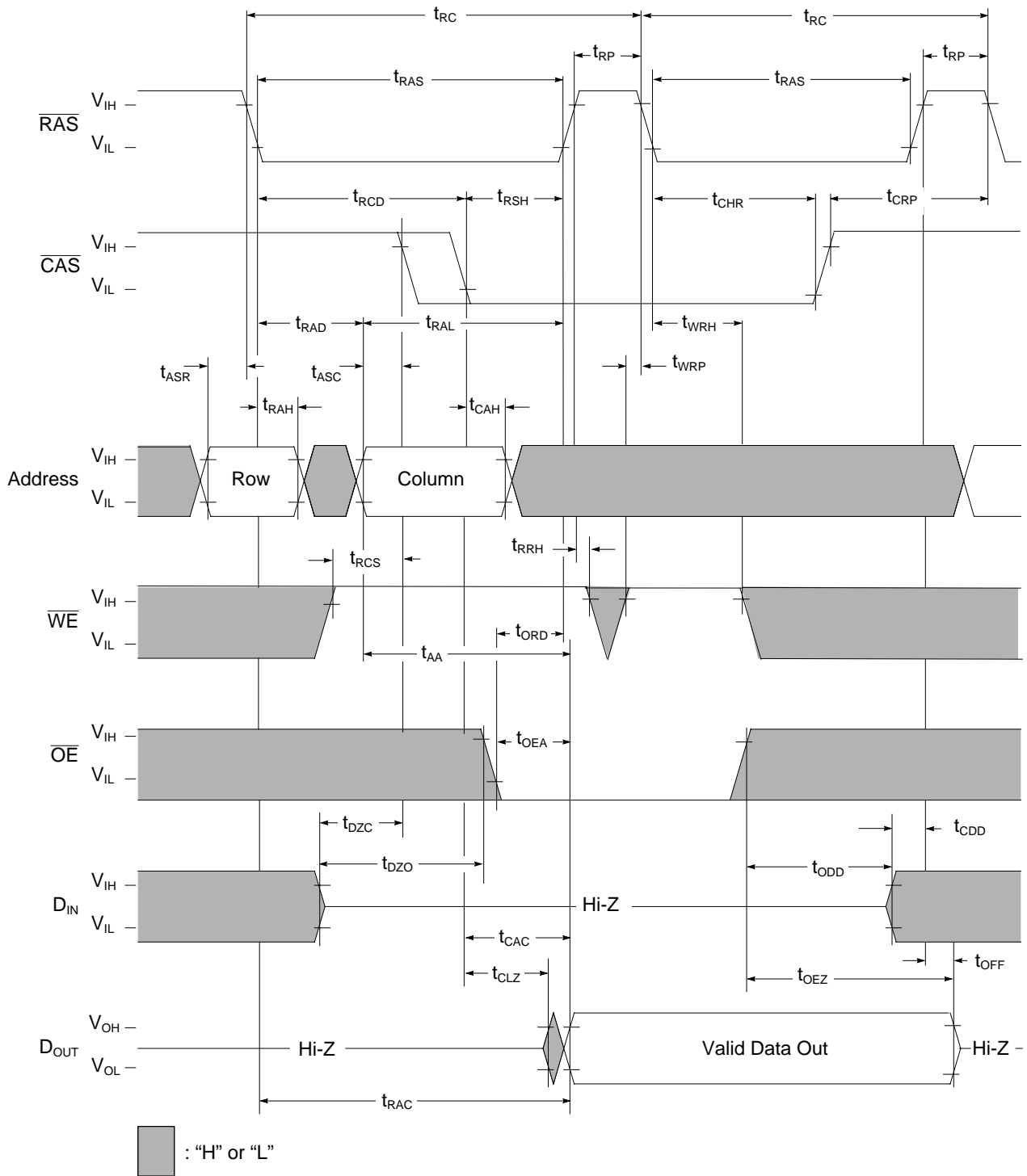


NOTE: Address is "H" or "L"



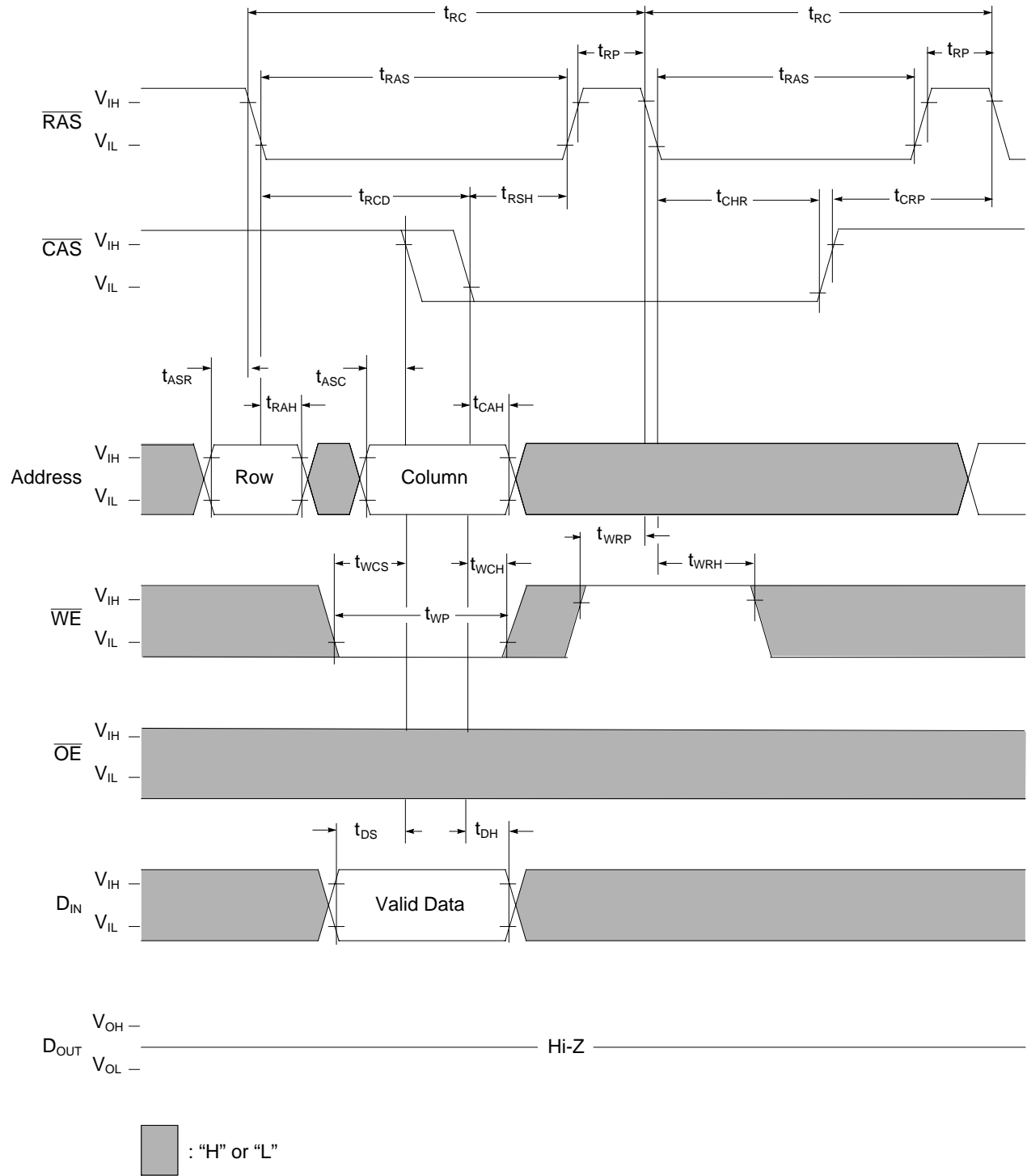
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Hidden Refresh Cycle (Read)

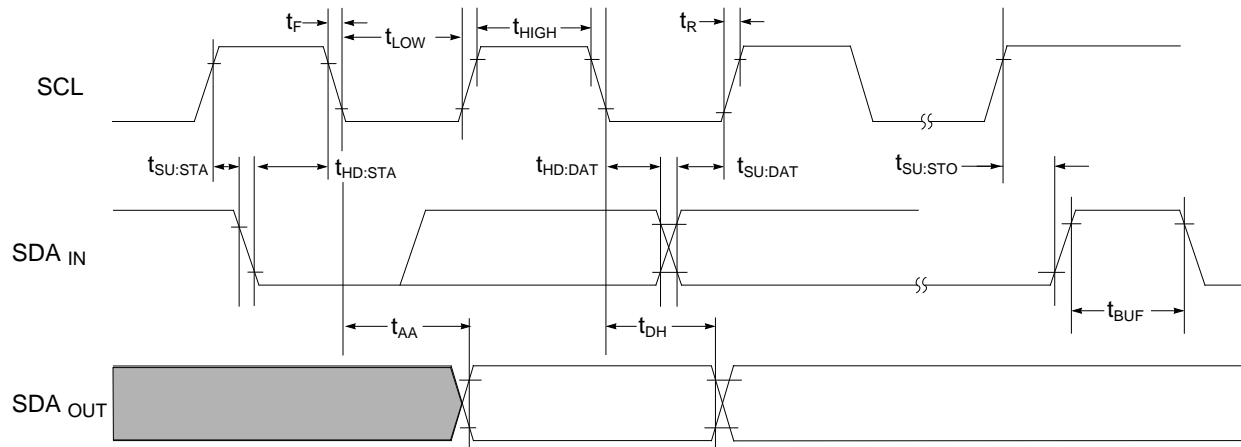




Hidden Refresh Cycle (Write)



Presence Detect (EEPROM) Bus Timing



Presence Detect Operation

Clock and Data Conventions: Data states on the SDA line can change only during SCL low. SDA state changes during SCL HIGH are reserved for indicating start and stop conditions (Figure 1 & Figure 2).

Start Condition: All commands are preceded by the start condition, which is a HIGH to LOW transition of SDA when SCL is high. The serial PD device continuously monitors the SDA and SCL lines for the start condition and will not respond to any command until this condition has been met.

Stop Condition: All communications are terminated by a stop condition, which is a LOW to HIGH transition of SDA when SCL is HIGH. The stop condition is also used to place the serial PD device into standby power mode.

Acknowledge: Acknowledge is a software convention used to indicate successful data transfers. The transmitting device, either master or slave, will release the bus after transmitting eight bits. During the ninth clock cycle the receiver will pull the SDA line LOW to acknowledge that it received the eight bits of data (Figure 3).

The PD device will always respond with an acknowledge after recognition of a start condition and its slave address. If both the device and a write operation have been selected, The PD device, will respond with an acknowledge after the receipt of each subsequent eight bit word. In the read mode the PD device will transmit eight bits of data, release the SDA line and monitor the line for an

acknowledge. If an acknowledge is detected and no stop condition is generated by the master, the slave will continue to transmit data. If an acknowledge is not detected, the slave will terminate further data transmissions and await the stop condition to return to standby power mode.

Figure 1. Data Window

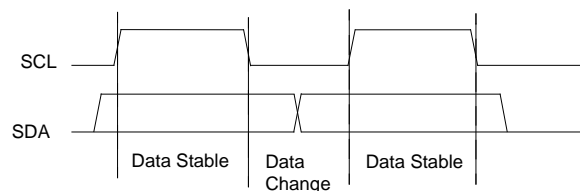


Figure 2. Definition of Start & Stop

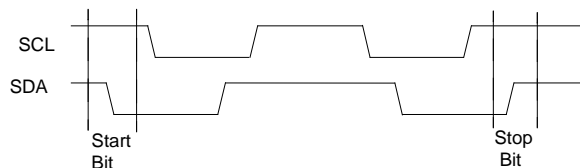
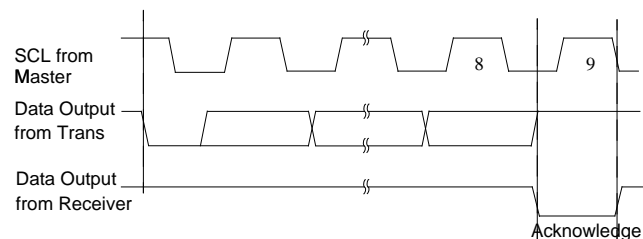
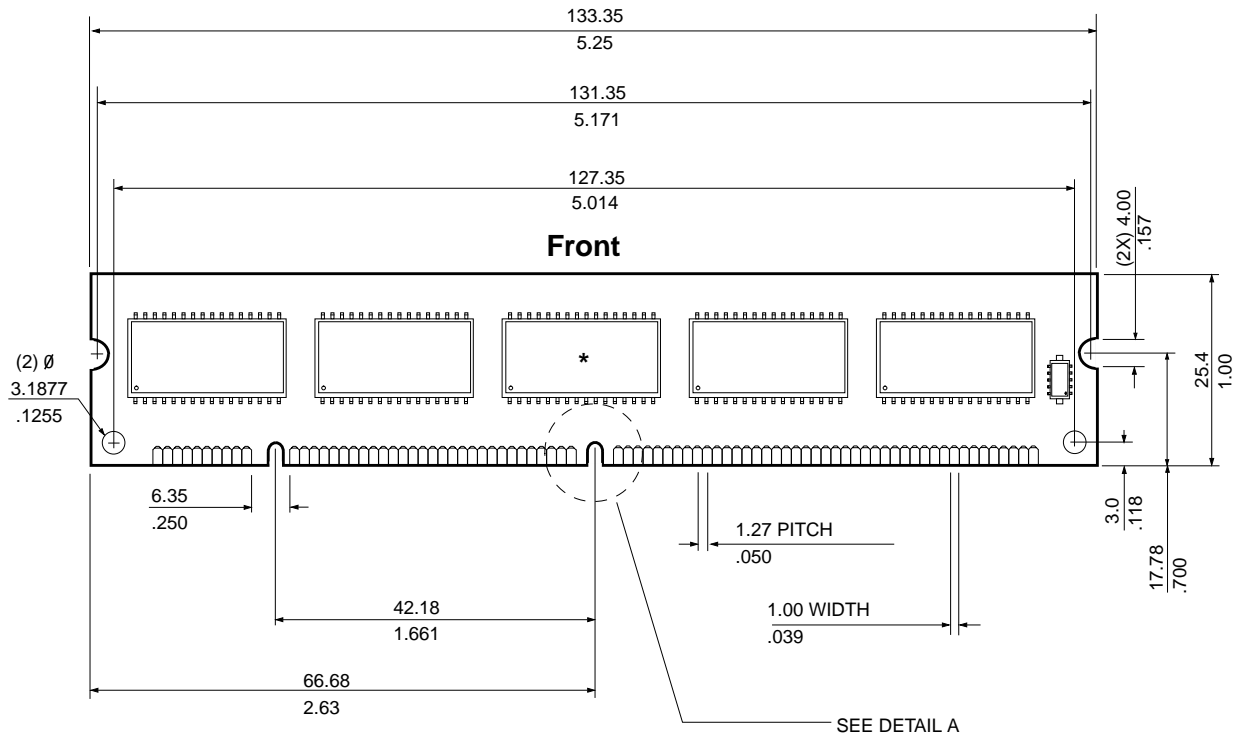


Figure 3. Acknowledge Response From Receiver

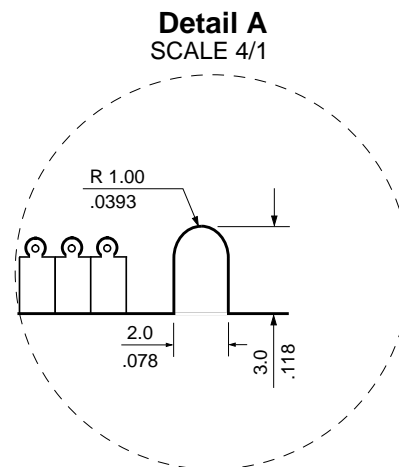
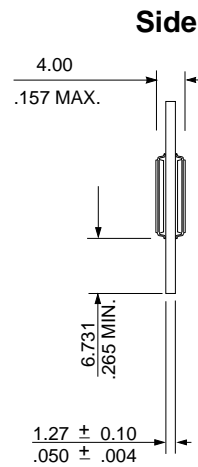




Layout Drawing



* On x72 only (CBx)



Note: All dimensions are typical unless otherwise stated.

Millimeters
 Inches



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Revision Log

Rev	Contents of Modification
3/96	Initial Release
5/96	Updated I _{CC} current: I _{CC5}
8/96	Updated capacitance table
12/96	Updated design with 400mil DRAM pkg Updated serial PD table
3/97	Updated Serial Presence Detect table
4/98	Added 50ns speed sort

Discontinued (9/98 - last order; 3/99 last ship)



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